RF3165

3V 1750MHZ W-CDMA LINEAR POWER AMPLIFIER MODULE

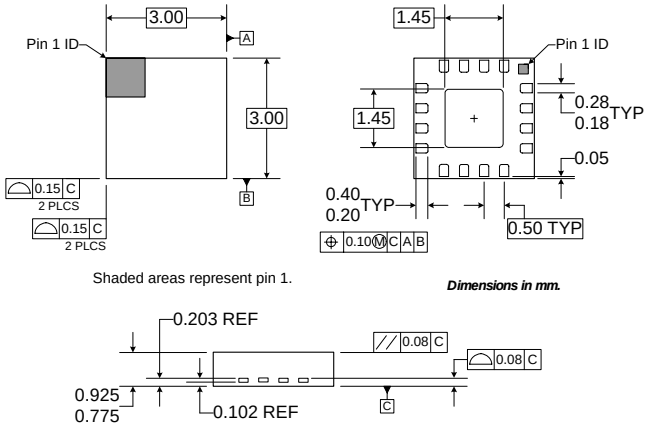
RoHS Compliant & Pb-Free Product

Typical Applications

- 3V W-CDMA Band 3, 4, and 9 Handsets
- Multi-Mode W-CDMA 3G Handsets
- Spread-Spectrum Systems

Product Description

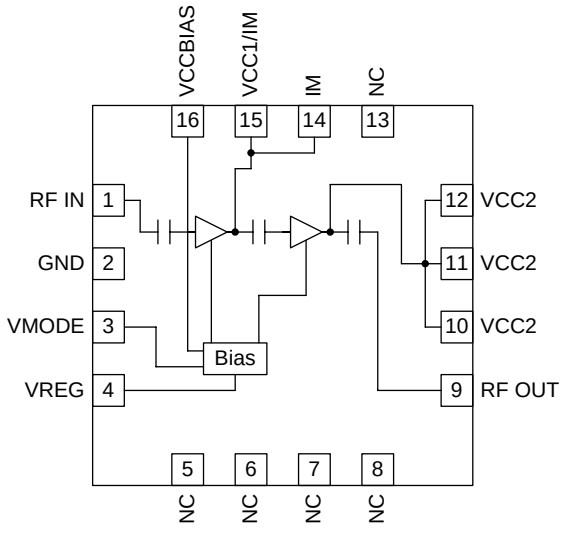
The RF3165 is a high-power, high-efficiency linear amplifier module specifically designed for 3V handheld systems. The device is manufactured on an advanced third generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V W-CDMA handheld digital cellular equipment, spread-spectrum systems, and other applications in the 1710MHz to 1785MHz band (Band 3). The RF3165 has a digital control line for low power applications to lower quiescent current. The RF3165 is assembled in at 16-pin, 3mmx3mm, QFN package.



Optimum Technology Matching® Applied

- ☐ Si BJT
- ☑ GaAs HBT
- ☐ GaAs MESFET
- ☐ Si Bi-CMOS
- ☐ SiGe HBT
- ☐ Si CMOS
- ☐ InGaP/HBT
- ☐ GaN HEMT
- ☐ SiGe Bi-CMOS

Package Style: QFN, 16-Pin, 3x3



Functional Block Diagram

Features

- Input/Output Internally Matched@50Ω
- 28dBm Linear Output Power
- 42% Peak Linear Efficiency
- 28dB Linear Gain
- -41dBc ACLR @ ±5MHz
- HSDPA Capable

Ordering Information

RF3165	3V 1750MHz W-CDMA Linear Power Amplifier Module
RF3165PCBA-410	Fully Assembled Evaluation Board

RF Micro Devices, Inc.
7628 Thorndike Road
Greensboro, NC 27409, USA
Tel (336) 664 1233
Fax (336) 664 0454
http://www.rfmd.com

Absolute Maximum Ratings

Parameter	Rating	Unit
Supply Voltage (RF off)	+8.0	V
Supply Voltage ($P_{OUT} \leq 31$dBm)	+5.2	V
Control Voltage (V_{REG})	+3.9	V
Input RF Power	+10	dBm
Mode Voltage (V_{MODE})	+3.9	V
Operating Temperature	-30 to +110	°C
Storage Temperature	-40 to +150	°C
Moisture Sensitivity Level IPC/JEDEC J-STD-20	MSL 2 @260	°C

Caution! ESD sensitive device.

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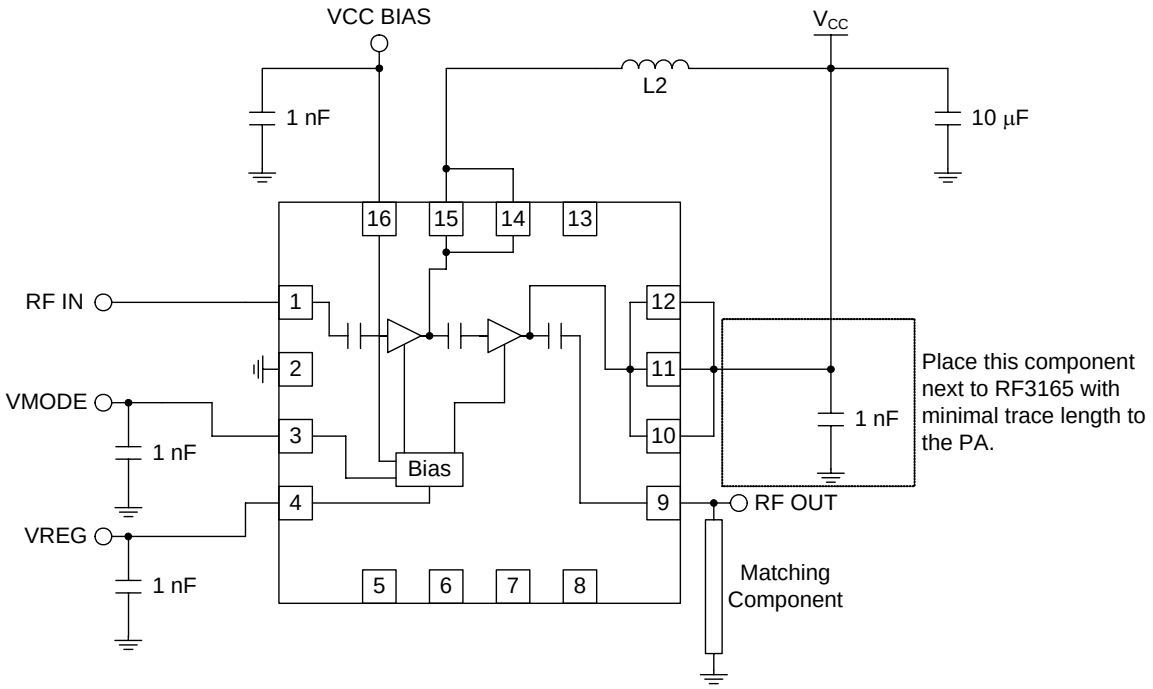
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
High Gain Mode (V_{MODE} Low)					T=25°C Ambient, V_{CCBIAS}=3.4V, V_{CC}=3.4V, V_{REG}=2.8V, V_{MODE}=0V, and P_{OUT}=28dBm for all parameters (unless otherwise specified). Modulation is 3GPP 3.2 03-00 DPCCH+1DPDCH.
Operating Frequency Range	1710		1785	MHz	
Linear Gain		28		dB	
Harmonics		-15		dBm	f=2fo, 3fo
Maximum Linear Output	28			dBm	
Linear Efficiency		42		%	
Maximum I_{CC}		442		mA	
ACLR1 @ ±5MHz		-41		dBc	
ACLR2 @ ±10MHz		-51		dBc	
Input VSWR		2:1			
Output VSWR Stability			6:1		No oscillation>-70dBc
			10:1		No damage
Noise Power		-146		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=925MHz to 960MHz (Band 8)
		-115		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=1805MHz to 1880MHz (Band 3 and 9)
		-144		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=2110MHz to 2170MHz (Band 1 and 4)
		-151		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=2400MHz to 2480MHz (Bluetooth)
		-156		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=869MHz to 894MHz (Band 5 and 6)
		-140		dBm/Hz	-50≤P_{OUT}≤+28dBm, RX=1930MHz to 1990MHz (Band 2)
IM Products					
IM 5MHz		-41	-31	dBc	IF offset f_O+5MHz with CW signal=-40dBc
IM 10MHz		-51	-41	dBc	IF offset f_O+10MHz with CW signal=-40dBc

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Low Gain/Low V_{CC} Mode (V_{MODE} High)					T=25°C Ambient, V_{CCBIAS}=3.4V, V_{CC}=1.5V, V_{REG}=2.8V, V_{MODE}=2.8V, and P_{OUT}=16dBm for all parameters (unless otherwise specified). Modulation is 3GPP 3.2 03-00 DPCCH+1DPDCH.
Operating Frequency Range	1710		1785	MHz	
Linear Gain		26		dB	
Maximum Linear Output				dBm	
Linear Efficiency		21.0		%	
ACLR @ ±5MHz		-40		dBc	
ACLR @ ±10MHz		-54		dBc	
Maximum I_{CC}		125		mA	
Input VSWR		2:1			
Output VSWR Stability			6:1		No oscillation>-65dBc
Ruggedness			10:1		No damage
IM Products					
IM 5MHz		-41	-31	dBc	IF offset f_O+5MHz with CW signal=-40dBc
IM 10MHz		-53	-41	dBc	IF offset f_O+10MHz with CW signal=-40dBc
Power Supply					
Supply Voltage (V_{CC1} and V_{CC2})	3.2	3.4	4.2	V	
	0.6			V	Low power with DC to DC Converter
V_{CC} Bias	1.5		4.2	V	
High Gain Idle Current (I_{CC1}/I_{CC2}/I_{CCBIAS})		70	93	mA	V_{MODE}=low and V_{REG}=2.8V, V_{CC}=3.4V
Low Gain Idle Current (I_{CC1}/I_{CC2}/I_{CCBIAS})		60	83	mA	V_{MODE}=high and V_{REG}=2.8V, V_{CC}=1.5V
V_{REG} Current		1	3	mA	
V_{MODE} Current		250		uA	
RF Turn On/Off Time		1.2	6	uS	
DC Turn On/Off Time		2	25	uS	
Total Current (Power Down)		0.2	0.5	uA	
V_{REG} Low Voltage (Power Down)	0		0.5	V	
V_{REG} High Voltage (Recommended)	2.75	2.8	2.95	V	
V_{REG} High Voltage (Operational)	2.7		3.0	V	
V_{MODE} Voltage	0		0.5	V	High Gain Mode
V_{MODE} Voltage	2.0		3.0	V	Low Gain Mode

Pin	Function	Description	Interface Schematic
1	RF IN	RF input internally matched to 50Ω. This input is internally AC-coupled.	
2	GND	Ground connection.	
3	VMODE	For nominal operation (High Power mode), V_{MODE} is set LOW. When set HIGH, devices are biased lower to improve efficiency at lower output levels.	
4	VREG	Regulated voltage supply for amplifier bias circuit. In power down mode, both V_{REG} and V_{MODE} need to be LOW (<0.5V).	
5	NC	No connection. Do not connect this pin to any external circuit.	
6	NC	No connection. Do not connect this pin to any external circuit.	
7	NC	No connection. Do not connect this pin to any external circuit.	
8	NC	No connection. Do not connect this pin to any external circuit.	
9	RF OUT	RF output. Internally AC-coupled.	
10	VCC2	Output stage collector supply. Connect to pin 11 with the shortest trace possible. Please see the schematic for required external components. See note.	
11	VCC2	Output stage collector supply and output matching. Connect to pin 10 and pin 12 with the shortest trace possible. See note.	
12	VCC2	Output stage collector supply and output matching. Connect to pin 11 with the shortest trace possible. See note.	
13	NC	No connection. Do not connect this pin to any external circuit.	
14	IM	Interstage matching. Connect to pin 15 with the shortest trace possible. See note.	
15	VCC1/IM	First stage collector supply and interstage matching. A 4.7μF decoupling capacitor may be required. Connect to pin 14 with the shortest trace possible. See note.	
16	VCCBIAS	Power supply input for the DC bias circuitry.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

Note: Refer to Layout Recommendation Application Note and Application Schematic for additional information.

Application Schematic



VCC BIAS can be connected to VCC; however, VCC must be maintained above 1.5 V.
L2 = 8.2 nH and may be needed to provide isolation between VCC1 and VCC2 depending on layout.

Circuit Optimization for Various Output Power Requirements

Output Power (dBm)	Matching Component	Sample Part Number	Typical Efficiency (%)
28.5	15nH	LQG15HN12NJ02D (Murata)	41
28	N/A		42
27.5	0.5pF	GRM1555C1HR50BZ01E (Murata)	42

Evaluation Board Schematic